



### 80V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	Rds(on)	I <sub>D</sub> T <sub>C</sub> = +25°C (Note 11)
80V	$3.8$ m $\Omega$ @ V <sub>GS</sub> = 10V	100A
	5.3mΩ @ V <sub>GS</sub> = 4.5V	100A

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low Rds(ON) Minimizes On-State Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

### **Description and Applications**

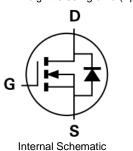
This new generation MOSFET is designed to minimize R<sub>DS(ON)</sub>, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

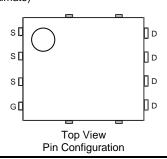
- DC-DC Converters
- Load Switch

### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)







### **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMTH8004LPS-13	PowerDI5060-8	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



);; = Manufacturer's Marking
TH8004LPS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 19 = 2019)
WW = Week (01 to 53)

December 2019

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## **Maximum Ratings** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			VDSS	80	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, $V_{GS} = 10V$ (Note 7)  Steady State $T_C = +25^{\circ}C$ $T_C = +100^{\circ}C$ (Note 11)			lo	100 100	А
Maximum Continuous Body Diode Forward Current (Note 7)			Is	83	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	400	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			Ism	400	Α
Avalanche Current, L = 0.3mH (Note 8)			I <sub>AS</sub>	35	А
Avalanche Energy, L = 0.3mH (Note 8)			Eas	183.7	mJ

## Thermal Characteristics (@Tc = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	101	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	51	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	125	W
Thermal Resistance, Junction to Case (Note 7)		Rejc	1.2	°C/W
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +175	°C

## Electrical Characteristics (@Tc = +25°C, unless otherwise specified.)

			,				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS		_	1	μΑ	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	Igss	_	_	±100	nA	V <sub>G</sub> S = ±20V, V <sub>D</sub> S = 0V	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	_	2.8	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	Descent	_	2.8	3.8	0	V <sub>G</sub> S = 10V, I <sub>D</sub> = 20A	
Static Dialii-Source Off-Resistance	RDS(ON)		3.9	5.3	mΩ	$V_{GS} = 4.5V, I_{D} = 20A$	
Diode Forward Voltage	$V_{SD}$	_	0.8	1.2	٧	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>	_	4979	_		101/11/	
Output Capacitance	Coss	_	1166	_	pF	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz	
Reverse Transfer Capacitance	Crss		71	_			
Gate Resistance	R <sub>G</sub>	_	2.1	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (VGS = 4.5V)	Q <sub>G</sub>		43	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_{G}$	_	81	_	nC	V <sub>DD</sub> = 40V. I <sub>D</sub> = 20A	
Gate-Source Charge	Qgs	_	14	_	IIC	VDD = 40V, ID = 20A	
Gate-Drain Charge	Q <sub>GD</sub>	_	22	_			
Turn-On Delay Time	t <sub>D</sub> (ON)	_	8.5	_			
Turn-On Rise Time	tR	_	11.8	_	20	$V_{DD} = 40V, V_{GS} = 10V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	55	_	ns	$I_D = 20A, R_G = 1.6\Omega$	
Turn-Off Fall Time	tF	_	27.7	_			
Body Diode Reverse Recovery Time	trr	_	53	_	ns	I= 200 di/dt 1000/up	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	91	_	nC	$I_F = 20A$ , di/dt = 100A/ $\mu$ s	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25$ °C.
- S. Jas and Lag ratings are based on how inequency and duty cycle
   Short duration pulse test used to minimize self-heating effect.
   Guaranteed by design. Not subject to product testing.
   Package limited.



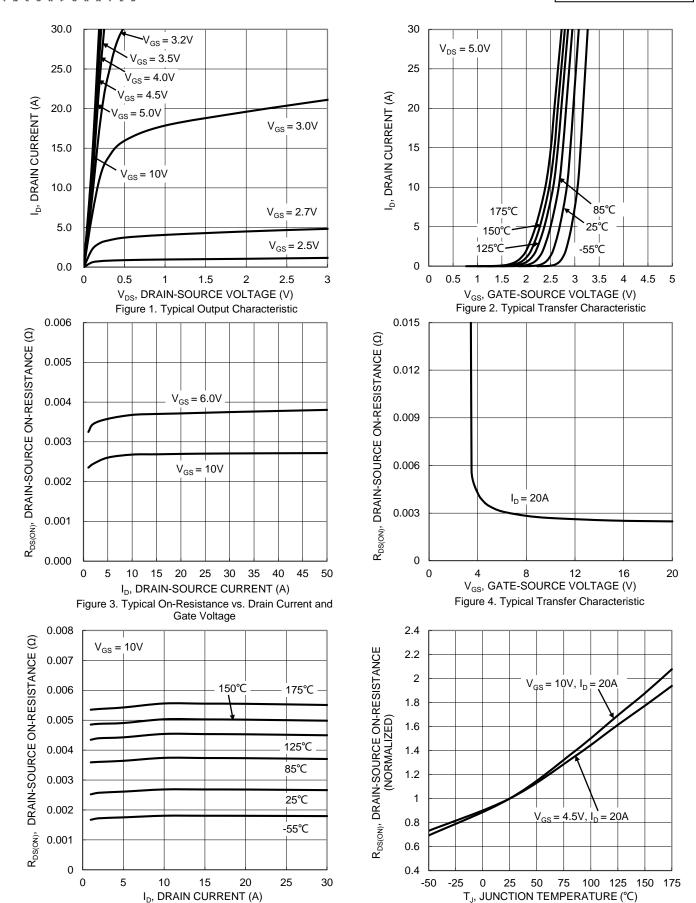


Figure 5. Typical On-Resistance vs. Drain Current and

Temperature

Figure 6. On-Resistance Variation with Temperature



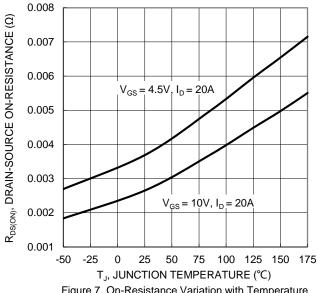


Figure 7. On-Resistance Variation with Temperature

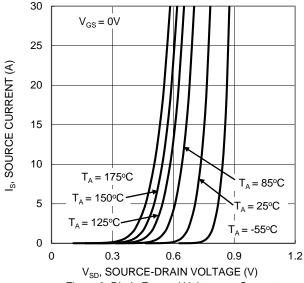
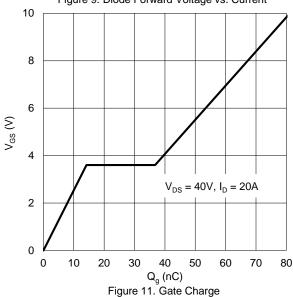
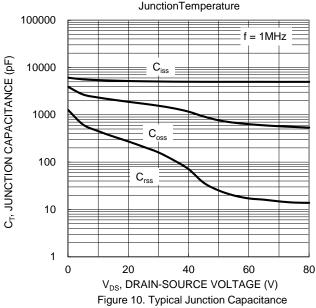
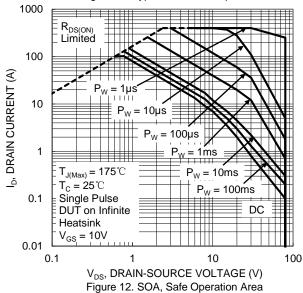


Figure 9. Diode Forward Voltage vs. Current



3 2.8  $V_{GS(TH)}, \text{ GATE THRESHOLD VOLTAGE (V)}$ 2.6 2.4 2.2 2  $I_D = 1mA$ 1.8 1.6 1.4  $I_{D} = 250 \mu A$ 1.2 1 0.8 0.6 0.4 0.2 0 -50 -25 25 50 75 100 125 150 175  $T_J$ , JUNCTION TEMPERATURE (°C) Figure 8. Gate Threshold Variation vs.







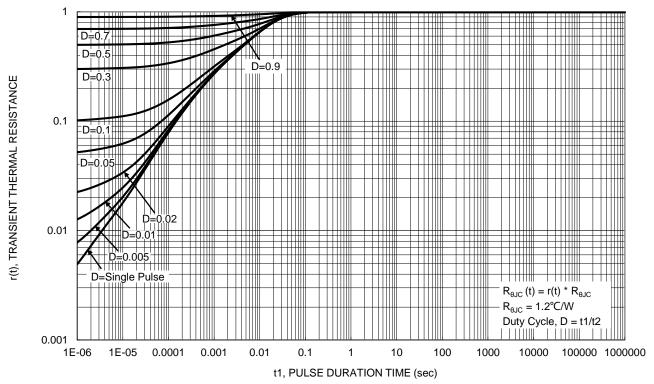


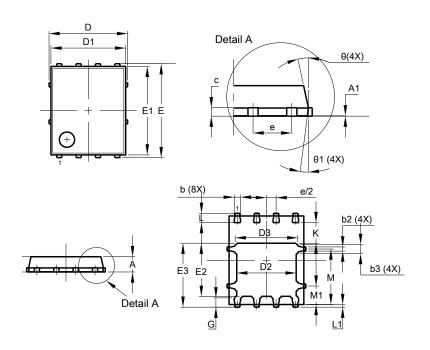
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

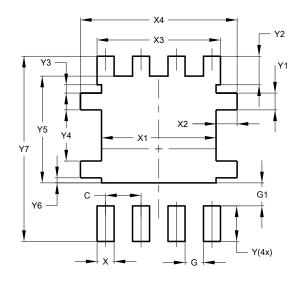


PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D	;	5.15 BSC	;		
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	(	6.15 BSC	;		
E1	5.60	5.60 6.00			
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е		1.27 BSC	;		
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All	All Dimensions in mm				

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
X	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Y	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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